| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|----------|------|--|---|---------------------|---------|------------------|
| Li | 1 | ("6716666").PN. | USPAT | OR | OFF | 2005/06/12 23:08 |
| L2 | 79 | (@ad<"20021224") and 438/445. ccls. and polysilicon | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/13 00:14 |
| L3 | 34 | (@ad<"20021224") and 438/446. , ccls. and polysilicon | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 23:17 |
| L4 | 292 | (@ad<"20021224") and ((fill or insert or coat or deposit or deposition or sputter\$4 or "cvd") with ((sidewall adj spacer\$1) and polysilicon)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/13 00:13 |
| L5 | 421 | (@ad<"20021224") and ((fill\$3 or insert or coat or deposit or deposition or sputter\$4 or "cvd") with ((sidewall adj spacer\$1) and polysilicon)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 23:59 |
| L6 | 380 | L5 and gate | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 23:20 |
| L7 | 3 | L5 and 438/587.ccls. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 23:59 |
| L8 | 4818 | (@ad<"20021224") and 438/184, 211,250,216,303,366,446,585, 587,595,639,696,697.ccls. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/13 00:14 |
| L9 | 5716 | (@ad<"20021224") and 438/184, 211,250,216,303,361,430,446, 647,657,684,366,446,585,587, 595,639,696,697.ccls. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/13 00:14 |

| L10 | 63260 | L9 and (polycrystalline or polysilicon) (gate near oxide) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/13 00:15 |
|-----|-------|---|---|----|-----|------------------|
| L11 | 2396 | L9 and (polycrystalline or polysilicon) and (gate near oxide) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/13:00:17 |
| L12 | 1547 | L11 and (etch\$3 with (sidewall or nitride)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/13 00:17 |
| L13 | 0 | L12 and ((polycrystalline or polysilicon) and (aniotropic near etch\$4)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/13 00:18 |
| L14 | 650 | L12 and ((polycrystalline or polysilicon) and (anisotropic near etch\$4)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/13 00:18 |